BT152-400R

SCR

5 September 2018 Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier in a SOT78 (TO-220AB) plastic package intended for use in applications requiring very high inrush current capability and high thermal cycling performance.

2. Features and benefits

- High thermal cycling performance
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Very high current surge capability

3. Applications

- Ignition circuits
- Motor control
- Protection circuits e.g. SMPS inrush current
- Voltage regulation

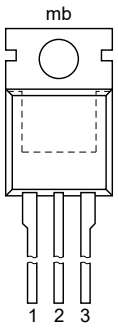
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	-	400	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 103$ °C; Fig. 1		-	-	13	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; Fig. 2; Fig. 3		-	-	20	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5		-	-	200	A
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms		-	-	220	A
T_j	junction temperature			-	-	125	°C
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 7		-	3	32	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 268 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12		200	300	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 TO-220AB (SOT78)	
2	A	anode		
3	G	gate		
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT152-400R	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	400	V
V_{RRM}	repetitive peak reverse voltage			-	400	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq$ 103 °C; Fig. 1		-	13	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; Fig. 2; Fig. 3		-	20	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5		-	200	A
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms		-	220	A
I^2t	I^2t for fusing	t_p = 10 ms; SIN		-	200	A²s
dI_T/dt	rate of rise of on-state current	I_G = 100 mA		-	200	A/µs
I_{GM}	peak gate current			-	5	A
V_{RGM}	peak reverse gate voltage			-	5	V
P_{GM}	peak gate power			-	20	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.5	W
T_{stg}	storage temperature			-40	150	°C
T_j	junction temperature			-	125	°C

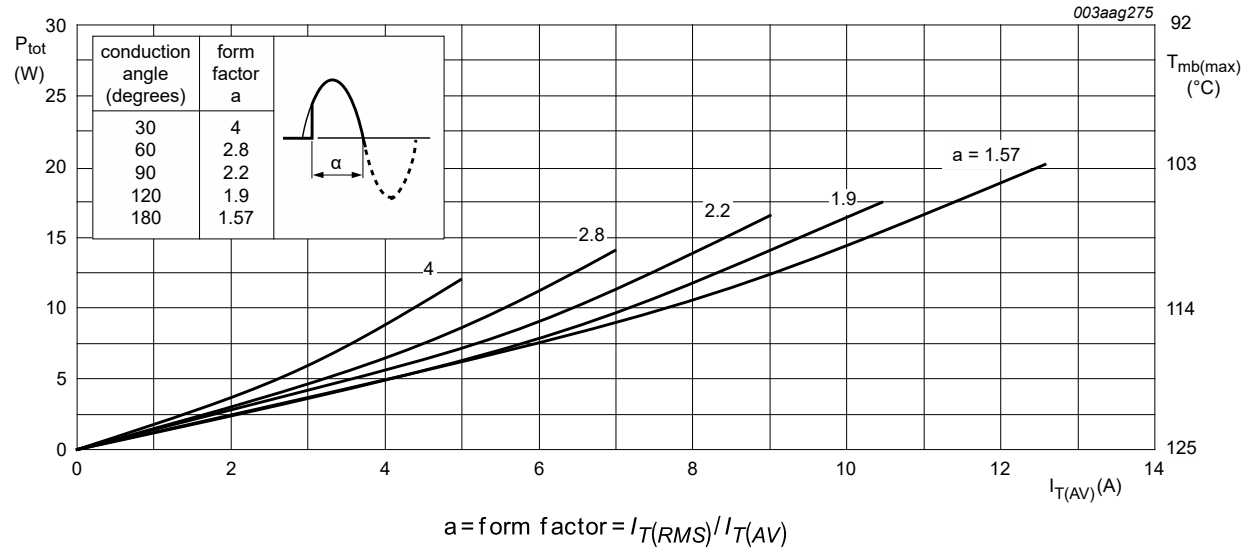


Fig. 1. Total power dissipation as a function of average on-state current; maximum values

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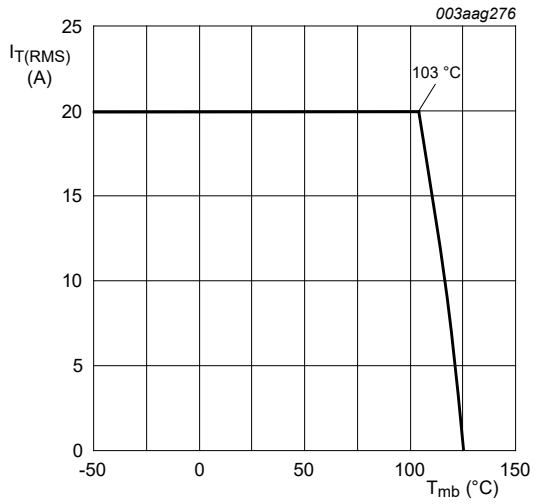
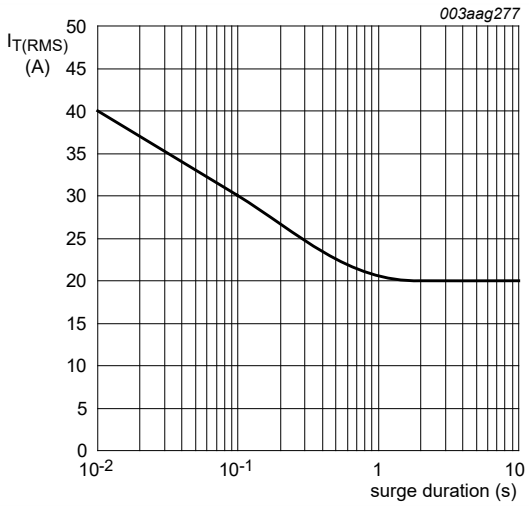
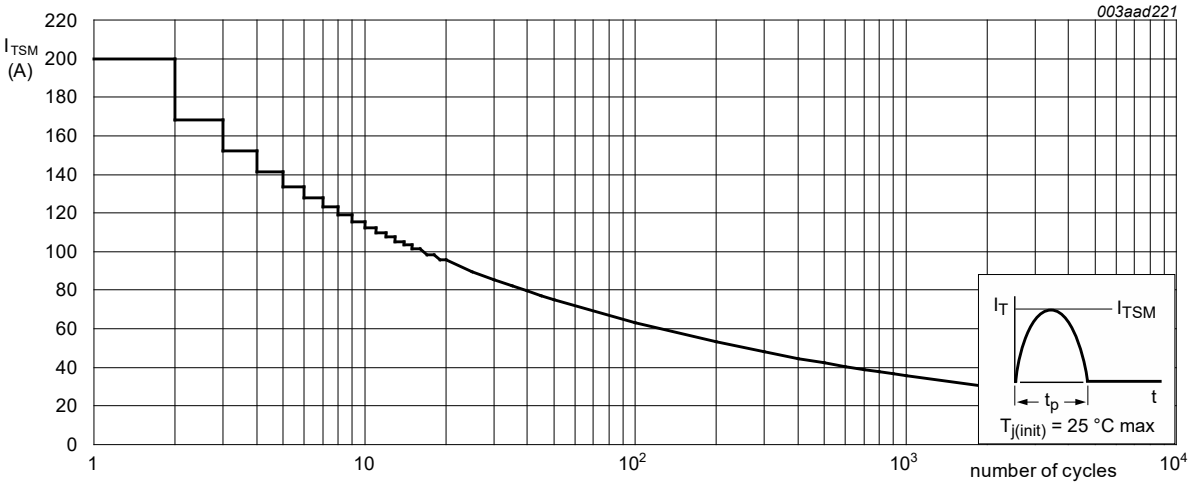


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz; T_{mb} = 103 °C

Fig. 3. RMS on-state current as a function of surge duration; maximum values

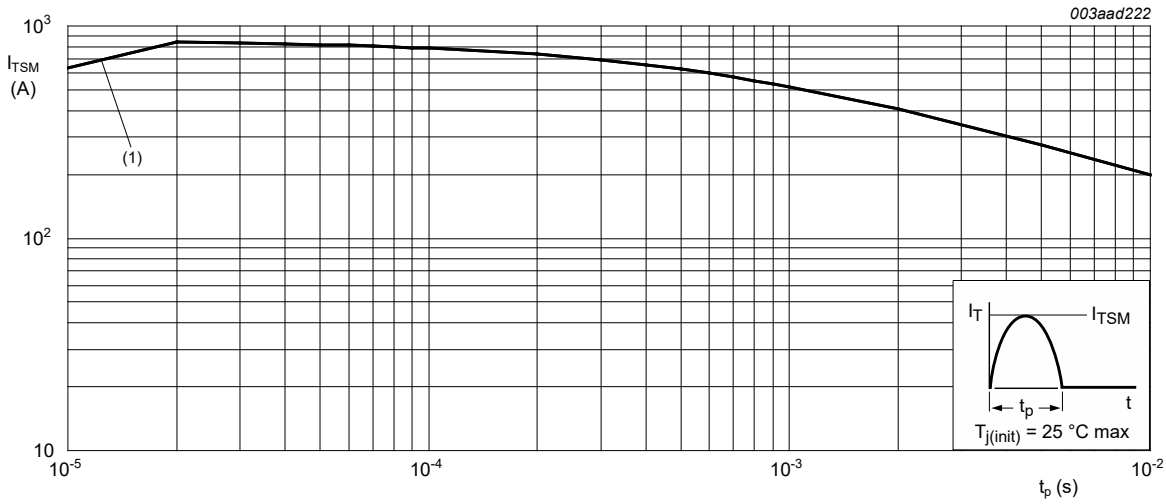


f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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$t_p \leq 10$ ms; (1) dI_T/dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 6		-	-	1.1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

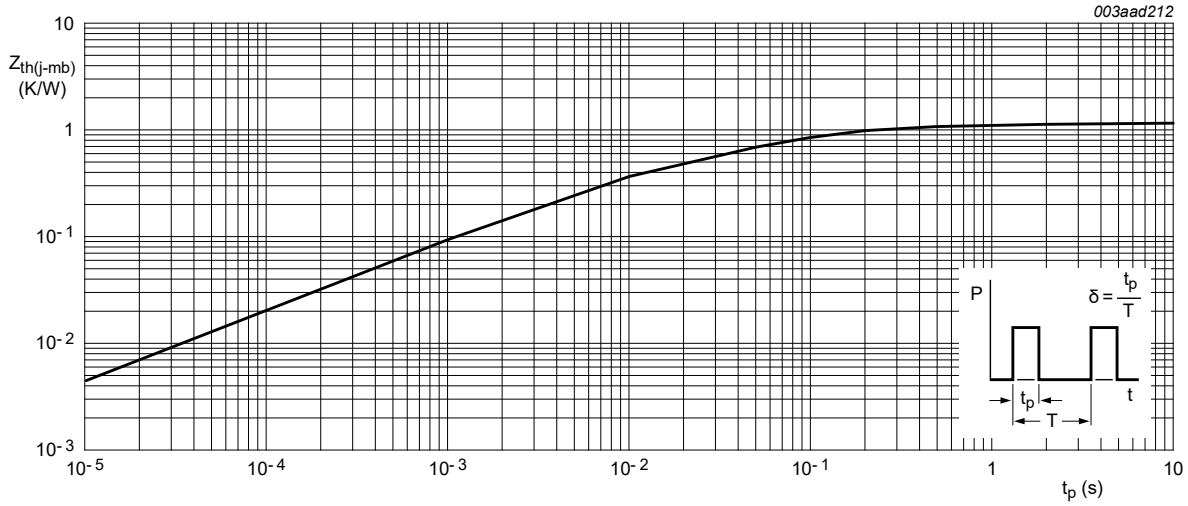


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 7		-	3	32	mA
I_L	latching current	V_D = 12 V; I_G = 0.1 A; T_j = 25 °C; Fig. 8		-	25	80	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	15	60	mA
V_T	on-state voltage	I_T = 40 A; T_j = 25 °C; Fig. 10		-	1.4	1.75	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 11		-	0.6	1	V
		V_D = 400 V; I_T = 0.1 A; T_j = 125 °C		0.25	0.4	-	V
I_D	off-state current	V_D = 400 V; T_j = 125 °C		-	0.2	1	mA
I_R	reverse current	V_R = 400 V; T_j = 125 °C		-	0.2	1	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 268 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12		200	300	-	V/µs
t_{gt}	gate-controlled turn-on time	I_{TM} = 40 A; V_D = 800 V; I_G = 100 mA; dI_G/dt = 5 A/µs		-	2	-	µs
t_q	commutated turn-off time	V_{DM} = 268 V; T_j = 125 °C; I_{TM} = 50 A; V_R = 25 V; $(dI_T/dt)_M$ = 30 A/µs; dV_D/dt = 50 V/µs; $R_{GK(ext)}$ = 100 Ω; (V_{DM} = 67% of V_{DRM})		-	70	-	µs

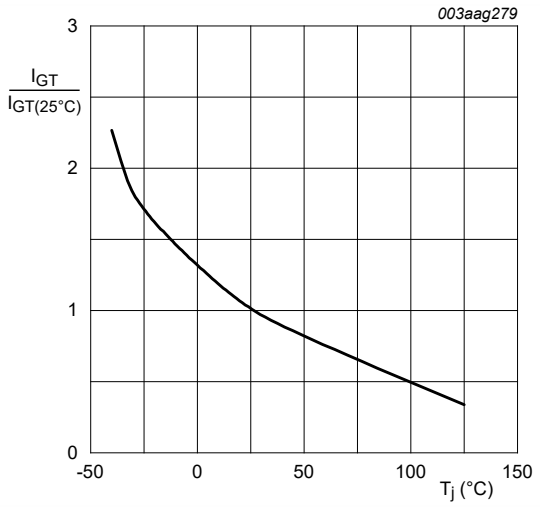


Fig. 7. Normalized gate trigger current as a function of junction temperature

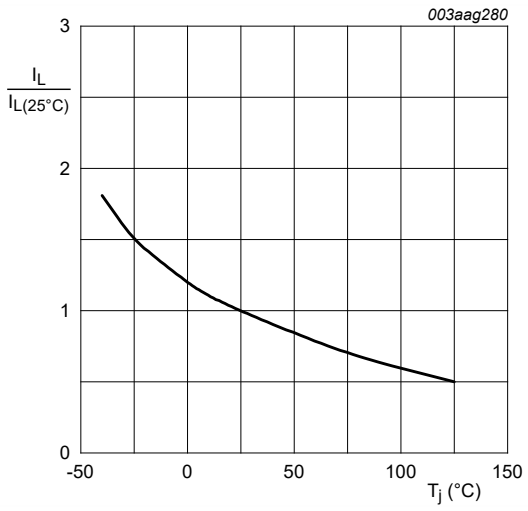


Fig. 8. Normalized latching current as a function of junction temperature

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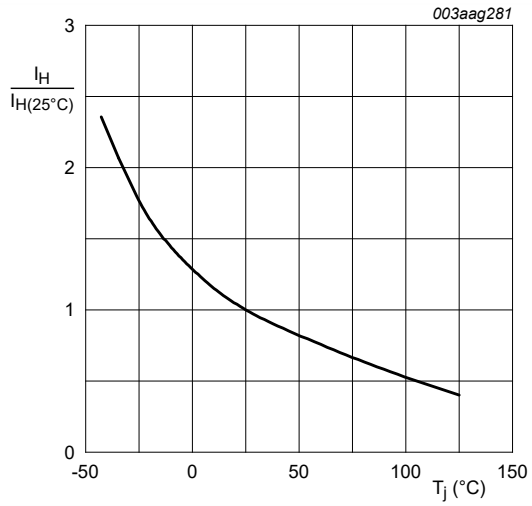
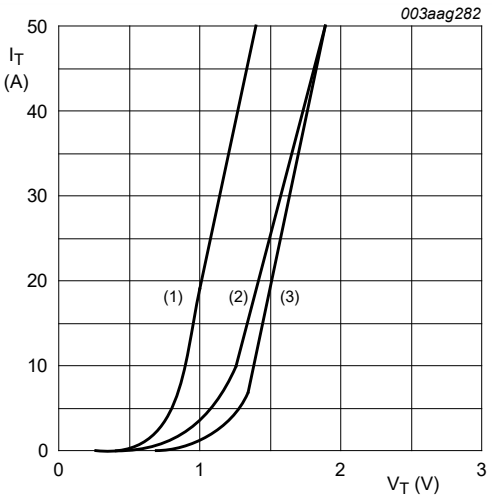


Fig. 9. Normalized holding current as a function of junction temperature



Vo = 1.06 V; Rs = 0.03 Ω
(1) Tj = 125 °C; typical values
(2) Tj = 125 °C; maximum values
(3) Tj = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

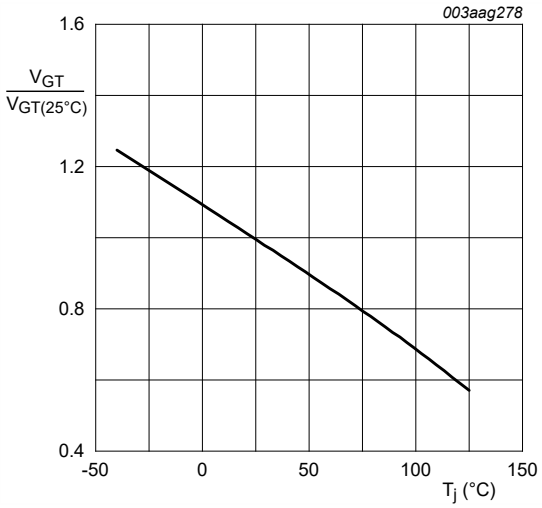
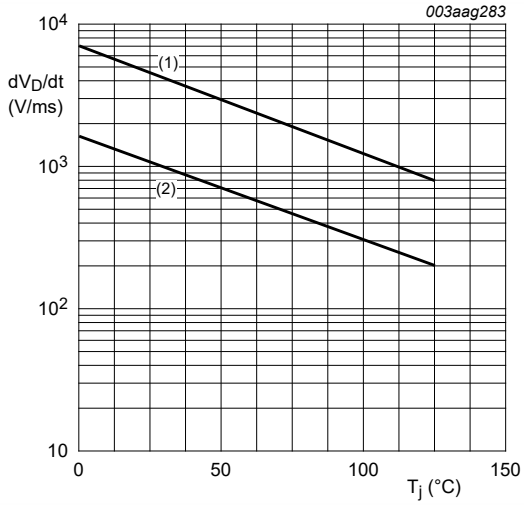


Fig. 11. Normalized gate trigger voltage as a function of junction temperature



(1) R_{GK} = 100 Ω
(2) Gate open circuit

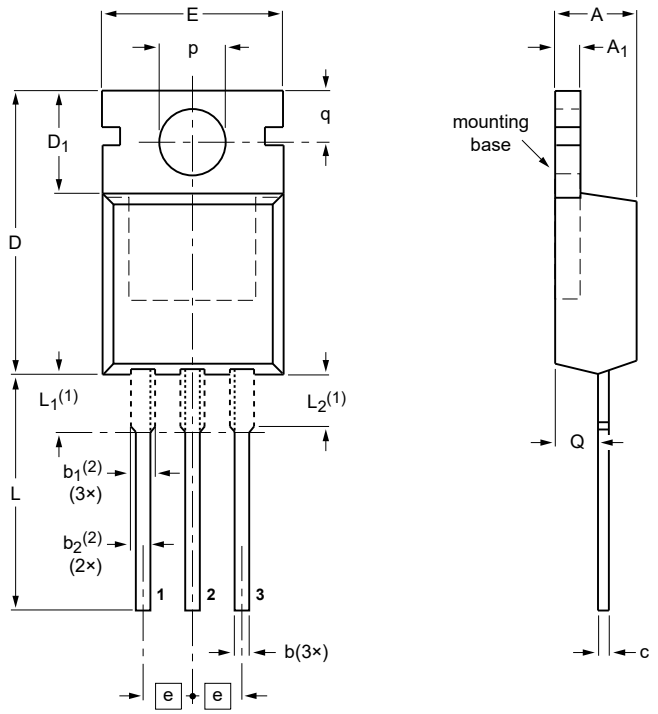
Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

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10. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1(2)	b_2(2)	c	D	D_1	E	e	L	L_1(1)	L_2(1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			~~08-04-23~~ 08-06-13

Fig. 13. Package outline TO-220AB (SOT78)

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12. Contents

1. General description....1
2. Features and benefits....1
3. Applications....1
4. Quick reference data....1
5. Pinning information....2
6. Ordering information....2
7. Limiting values....3
8. Thermal characteristics....6
9. Characteristics....7
10. Package outline....9
11. Legal information....10

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